

Automotive-grade N-channel 40 V, 3.0 mΩ typ., 55 A STripFET™ F6 Power MOSFET in a PowerFLAT™ 5x6 package

Datasheet - production data

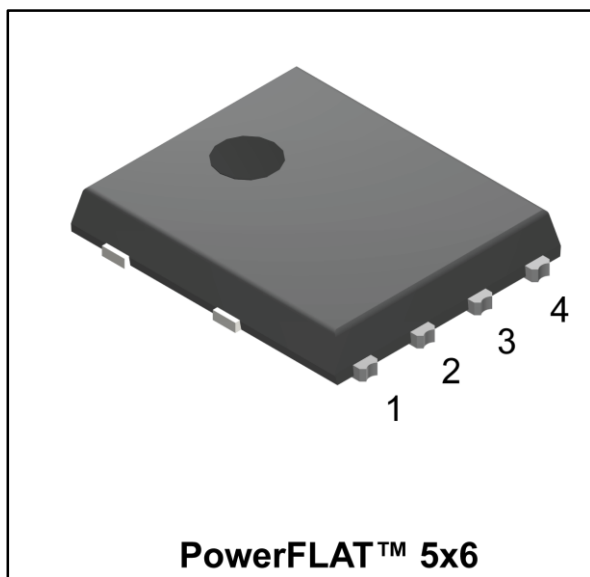
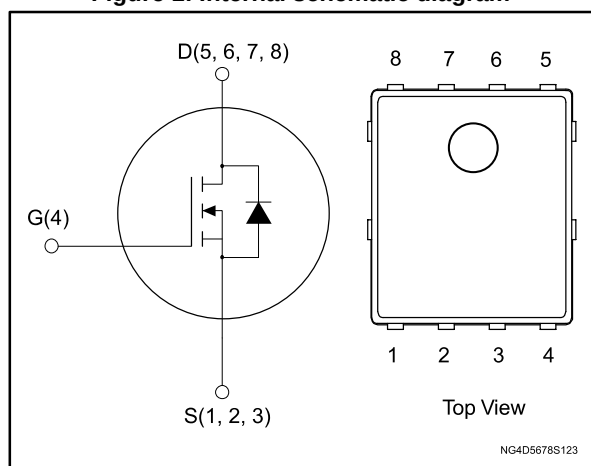


Figure 1: Internal schematic diagram



Features

Order code	V _{DS}	R _{DS(on)} max.	I _D	P _{TOT}
STL120N4LF6AG	40 V	3.6 mΩ	55 A	96 W

- Designed for automotive applications and AEC-Q101 qualified
- Very low on-resistance
- Very low gate charge
- High avalanche ruggedness
- Low gate drive power loss
- Wettable flank package

Applications

- Switching applications

Description

This device is an N-channel Power MOSFET developed using the STripFET™ F6 technology with a new trench gate structure. The resulting Power MOSFET exhibits very low R_{DS(on)} in all packages.

Table 1: Device summary

Order code	Marking	Package	Packing
STL120N4LF6AG	120N4LF6	PowerFLAT™ 5x6	Tape and reel

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1 Electrical ratings

Table 2: Absolute maximum ratings

Symbol	Parameter	Value	Unit
V_{GS}	Gate-source voltage	40	V
V_{DS}	Drain-source voltage	± 20	V
$I_D^{(1)}$	Drain current (continuous) at $T_C = 25\text{ }^{\circ}\text{C}$	55	A
$I_D^{(1)}$	Drain current (continuous) at $T_C = 100\text{ }^{\circ}\text{C}$	55	A
$I_{DM}^{(2)}$	Drain current (pulsed)	220	A
P_{TOT}	Total dissipation at $T_C = 25\text{ }^{\circ}\text{C}$	96	W
T_{stg}	Storage temperature range	- 55 to 175	$^{\circ}\text{C}$
T_j	Operating junction temperature range		$^{\circ}\text{C}$

Notes:

⁽¹⁾ Drain current is limited by package, the current capability of the silicon is 120 A at 25 $^{\circ}\text{C}$

⁽²⁾ Pulse width is limited by safe operating area

Table 3: Thermal data

Symbol	Parameter	Value	Unit
$R_{thj-case}$	Thermal resistance junction-case	1.56	$^{\circ}\text{C/W}$
$R_{thj-pcb}^{(1)}$	Thermal resistance junction-pcb	31.3	

Notes:

⁽¹⁾When mounted on 1 inch² 2 Oz. Cu board, $t \leq 10\text{ s}$

Table 4: Avalanche characteristics

Symbol	Parameter	Value	Unit
I_{AV}	Avalanche current, repetitive or not repetitive (pulse width limited by maximum junction temperature)	26	A
E_{AS}	Single pulse avalanche energy ($T_j = 25\text{ }^{\circ}\text{C}$, $I_C = I_{AV}$, $V_{DD} = 25\text{ V}$)	200	mJ

2 Electrical characteristics

(T_C = 25 °C unless otherwise specified)

Table 5: On/off states

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
V _{(BR)DSS}	Drain-source breakdown voltage	V _{GS} = 0 V, I _D = 250 μA	40			V
I _{DSS}	Zero gate voltage Drain current	V _{GS} = 0 V, V _{DS} = 40 V			1	μA
		V _{GS} = 0 V, V _{DS} = 40 V, T _J = 125 °C ⁽¹⁾			10	μA
I _{GSS}	Gate-body leakage current	V _{DS} = 0 V, V _{GS} = ±20 V			±100	nA
V _{GS(th)}	Gate threshold voltage	V _{DS} = V _{GS} , I _D = 250 μA	1		3	V
R _{DS(on)}	Static drain-source on-resistance	V _{GS} = 10 V, I _D = 13 A		3.0	3.6	mΩ
		V _{GS} = 5 V, I _D = 13 A		3.2	4.5	

Notes:

⁽¹⁾Defined by design, not subject to production test.

Table 6: Dynamic

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
C _{iss}	Input capacitance	V _{DS} = 25 V, f = 1 MHz, V _{GS} = 0 V	-	4260	-	pF
C _{oss}	Output capacitance		-	647	-	
C _{rss}	Reverse transfer capacitance		-	373	-	
Q _g	Total gate charge	V _{DD} = 20 V, I _D = 26 A, V _{GS} = 10 V (see Figure 14: "Test circuit for gate charge behavior")	-	80	-	nC
Q _{gs}	Gate-source charge		-	15	-	
Q _{gd}	Gate-drain charge		-	15	-	
R _G	Intrinsic gate resistance	f = 1 MHz, I _D = 0 A	-	1.5	-	Ω

Table 7: Switching times

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
t _{d(on)}	Turn-on delay time	V _{DD} = 20 V, I _D = 13 A R _G = 4.7 Ω, V _{GS} = 10 V (see Figure 13: "Test circuit for resistive load switching times" and Figure 18: "Switching time waveform")	-	20	-	ns
t _r	Rise time		-	70	-	
t _{d(off)}	Turn-off delay time		-	40	-	
t _f	Fall time		-	20	-	

Table 8: Source drain diode

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$I_{SD}^{(1)}$	Source-drain current		-		26	A
$I_{SDM}^{(2)}$	Source-drain current (pulsed)		-		104	A
$V_{SD}^{(3)}$	Forward on voltage	$V_{GS} = 0\text{ V}$, $I_{SD} = 13\text{ A}$	-		1.1	V
t_{rr}	Reverse recovery time	$I_{SD} = 26\text{ A}$, $di/dt = 100\text{ A}/\mu\text{s}$, $V_{DD} = 25\text{ V}$ (see Figure 15: "Test circuit for inductive load switching and diode recovery times")	-	40		ns
Q_{rr}	Reverse recovery charge		-	5.6		nC
I_{RRM}	Reverse recovery current		-	2.8		A

Notes:

⁽¹⁾This value is rated according to $R_{thj-pcb}$

⁽²⁾Pulse width is limited by safe operating area

⁽³⁾Pulse test: pulse duration = 300 μs , duty cycle 1.5%

2.1 Electrical characteristics (curves)

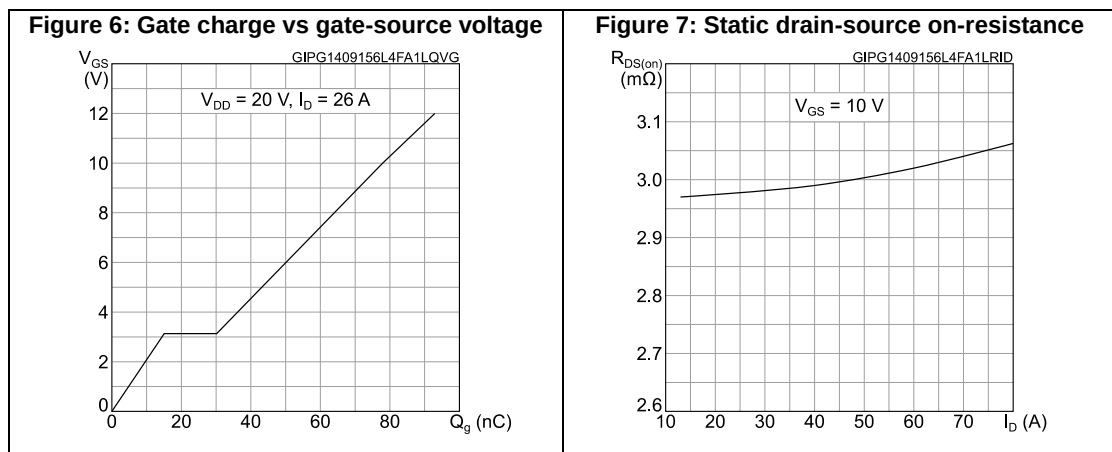
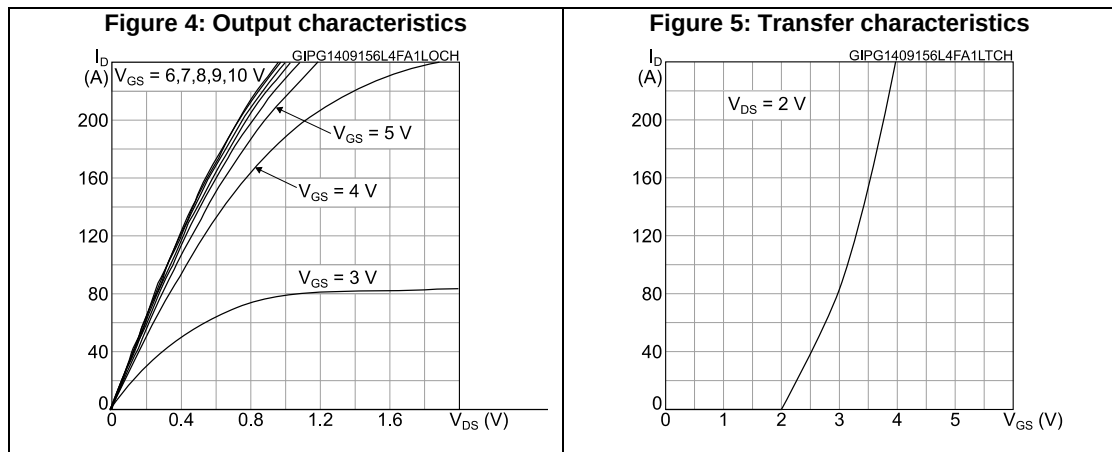
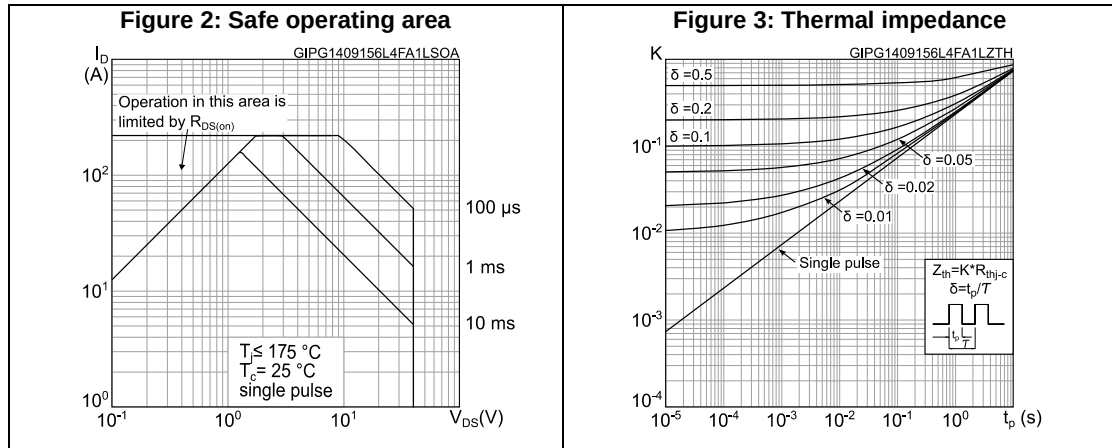


Figure 8: Capacitance variations

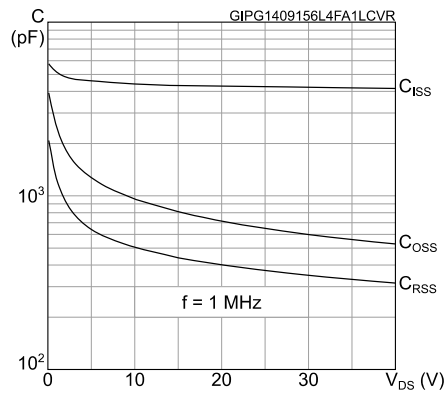


Figure 9: Normalized gate threshold voltage vs temperature

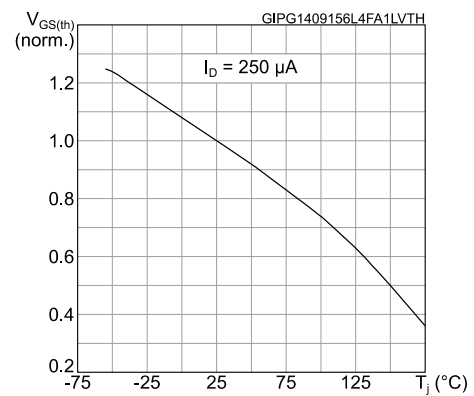


Figure 10: Normalized on-resistance vs temperature

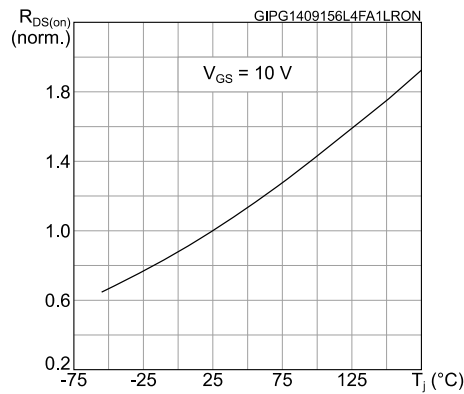


Figure 11: Normalized V(BR)DSS vs temperature

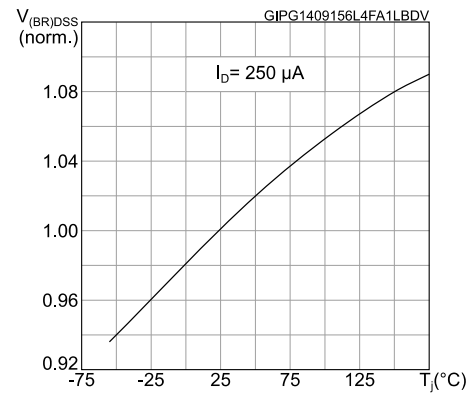
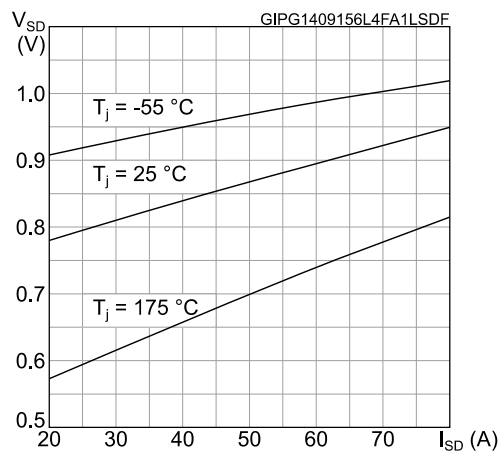
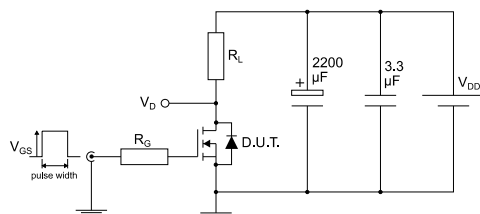


Figure 12: Source-drain diode forward characteristics



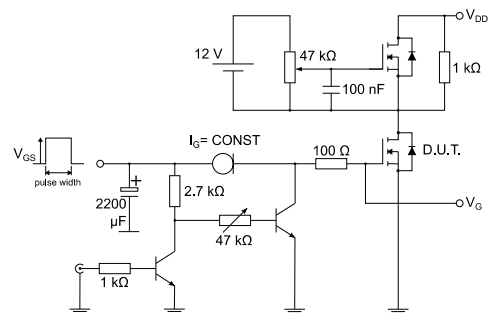
3 Test circuits

Figure 13: Test circuit for resistive load switching times



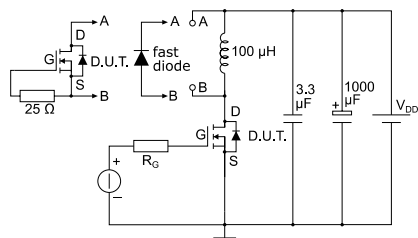
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Figure 14: Test circuit for gate charge behavior



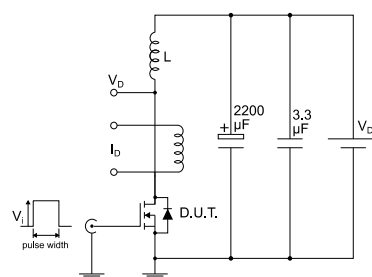
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Figure 15: Test circuit for inductive load switching and diode recovery times



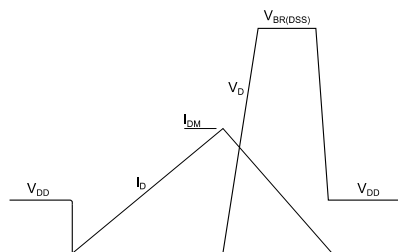
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Figure 16: Unclamped inductive load test circuit



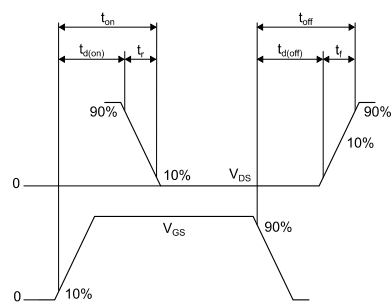
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Figure 17: Unclamped inductive waveform



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Figure 18: Switching time waveform



AM01473v1

4 Package information

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK® packages, depending on their level of environmental compliance. ECOPACK® specifications, grade definitions and product status are available at: www.st.com. ECOPACK® is an ST trademark.

4.1 PowerFLAT™ 5x6 WF type R package information

Figure 19: PowerFLAT™ 5x6 WF type R package outline

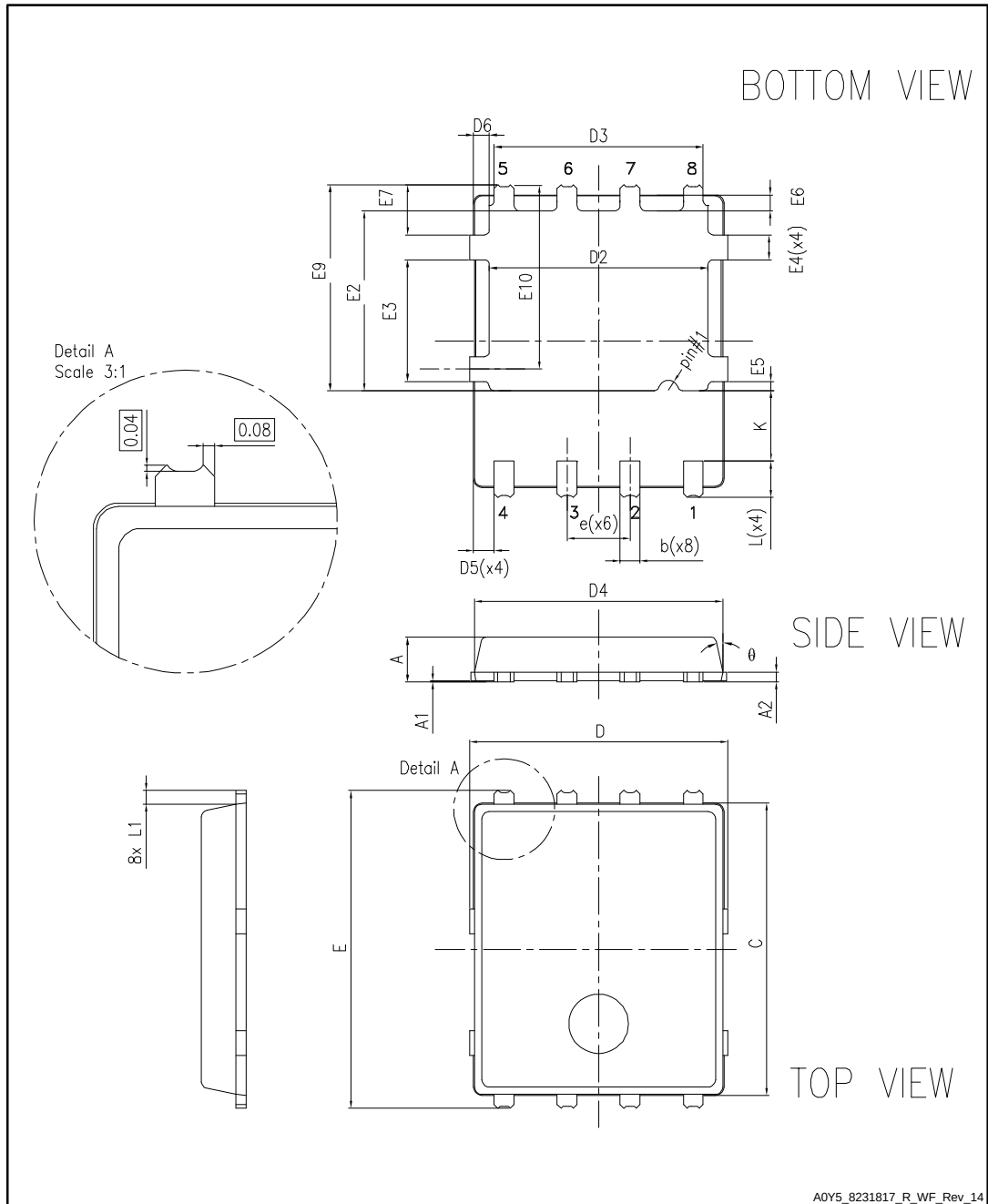
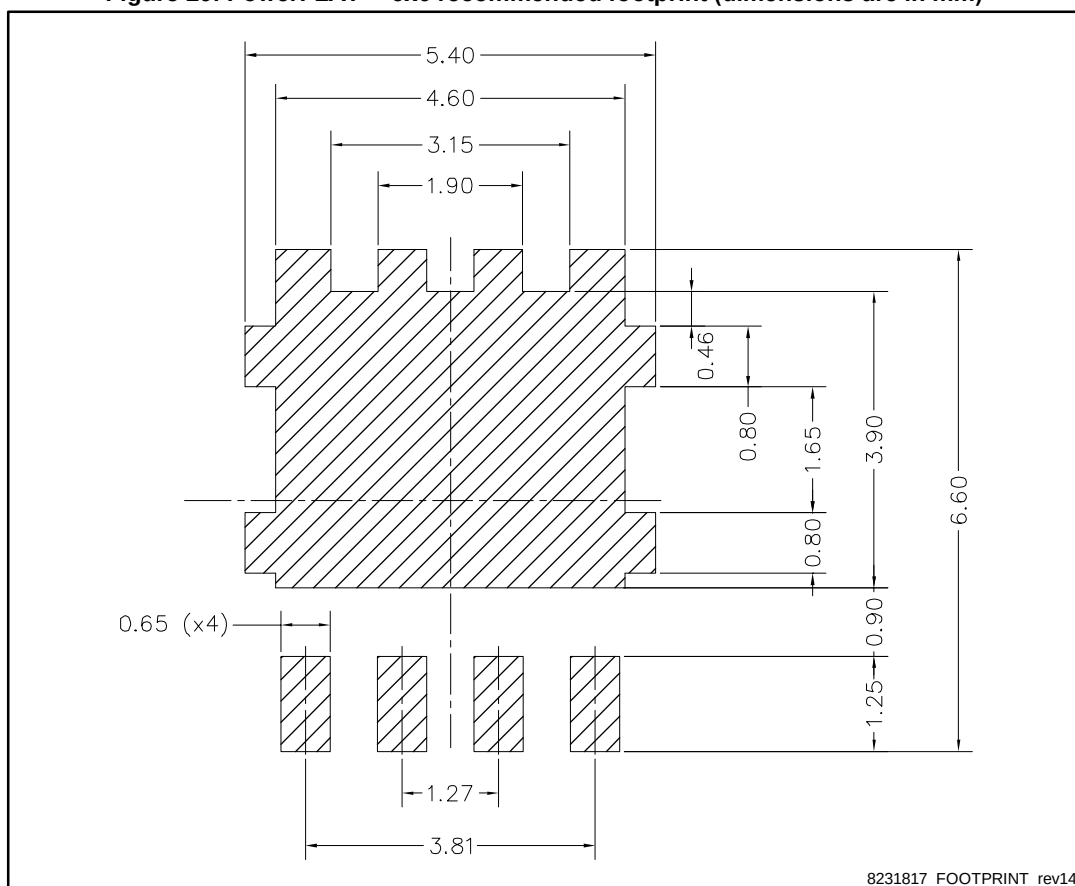


Table 9: PowerFLAT™ 5x6 WF type R mechanical data

Dim.	mm		
	Min.	Typ.	Max.
A	0.80		1.00
A1	0.02		0.05
A2		0.25	
b	0.30		0.50
C	5.80	6.00	6.10
D	5.00	5.20	5.40
D2	4.15		4.45
D3	4.05	4.20	4.35
D4	4.80	5.00	5.10
D5	0.25	0.4	0.55
D6	0.15	0.3	0.45
e		1.27	
E	6.20	6.40	6.60
E2	3.50		3.70
E3	2.35		2.55
E4	0.40		0.60
E5	0.08		0.28
E6	0.20	0.325	0.45
E7	0.85	1.00	1.15
E9	4.00	4.20	4.40
E10	3.55	3.70	3.85
K	1.275		1.575
L	0.725	0.825	0.925
L1	0.175	0.275	0.375
Θ	0°		12°

Figure 20: PowerFLAT™ 5x6 recommended footprint (dimensions are in mm)



4.2 PowerFLAT™ 5x6 WF packing information

Figure 21: PowerFLAT™ 5x6 WF tape (dimensions are in mm)

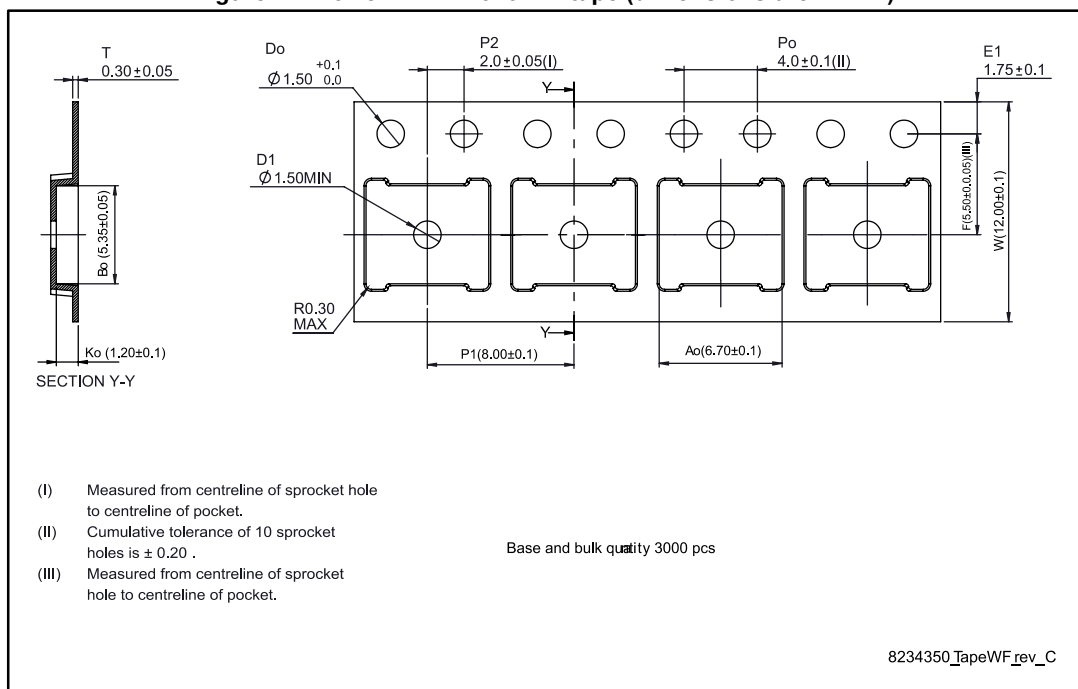


Figure 22: PowerFLAT™ 5x6 package orientation in carrier tape

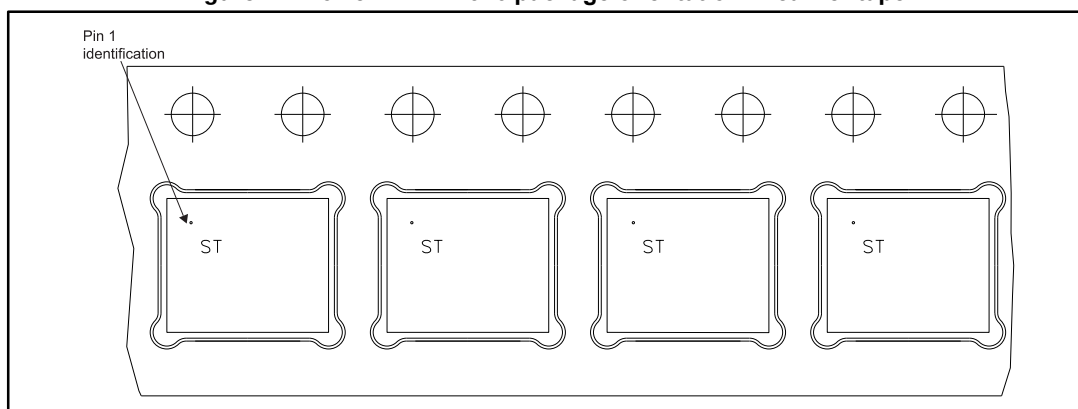
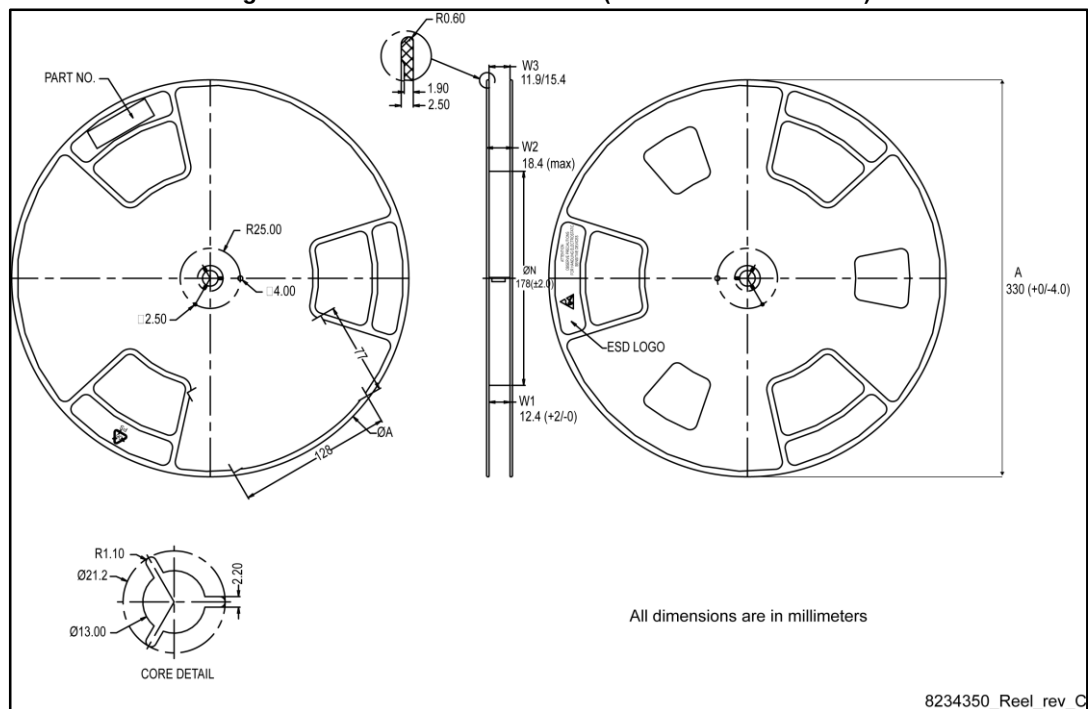


Figure 23: PowerFLAT™ 5x6 reel (dimensions are in mm)



5 Revision history

Table 10: Document revision history

Date	Revision	Changes
25-Sep-2015	1	First release.
15-Apr-2016	2	Updated title, description and features in cover page . Updated Table 2: "Absolute maximum ratings" and Table 5: "On/off states" . Minor text changes.

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